

Session Program

18-22 Jun 2017



2017 IEEE Pulsed Power Conference

Oral session 12 - Semiconductor components, Pulse Forming Networks and Alternate Technologies (part II) - Session Chair : Luis Redondo

Hilton Brighton Metropole Hotel
Kings Road Brighton BN1 2FU United Kingdom

Tuesday 20 June

15:00

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Session | **Location:** Hilton Brighton Metropole Hotel, Preston

15:00–15:30

Solid State Spark Gap and Ignitron Replacements

Speaker

John Waldron

15:30–15:45

HIGH-VOLTAGE PICOSECOND-RANGE AVALANCHE SWITCHING OF SEMICONDUCTOR STRUCTURES WITHOUT PN-JUNCTIONS

Speaker

Pavel Rodin

15:45–16:00

The Progression of Silicon Carbide Power Devices Under The Army's High Voltage Power Technology Program

Speaker

Dr Miguel Hinojosa

16:00–16:15

Study on the high-power semi-insulating GaAs PCSS with quantum well structure

Speaker

Dr Chongbiao Luan

16:15–16:30

Narrow Pulse Evaluation of 15 kV SiC MOSFETs and IGBTs

Speaker

Stephen Bayne

16:30–17:00

INVESTIGATION OF FAST THYRISTOR SWITCHING MODULES TRIGGERED BY DIRECT OVERHEAD IGNITION

Speaker

Rainer Bischoff

17:00–17:15

Silvaco-based evaluation of 10 kV 4H-SiC MOSFET as a solid-state switch in narrow-pulse application

Speaker

Dr Bejoy Pushpakaran

17:30